

**描述 / Descriptions**

TO-220            N    MOS            N-CHANNEL MOSFET in a TO-220 Plastic Package.

**特征 / Features**

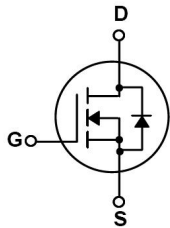
Low gate charge, Low Crss , Fast switching.

**用途 / Applications**

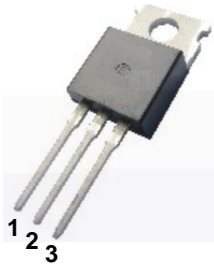
PFC

These devices are well suited for high efficient switched mode power supplies, active power factor correction, electronic lamp ballast based on half bridge topology.

**内部等效电路 / Equivalent Circuit**



**引脚排列 / Pinning**



PIN1 G            PIN 2 D            PIN 3 S

**放大及印章代码 / h<sub>FE</sub> Classifications & Marking**

See Marking Instructions.

**极限参数 / Absolute Maximum Ratings(Ta=25°C)**

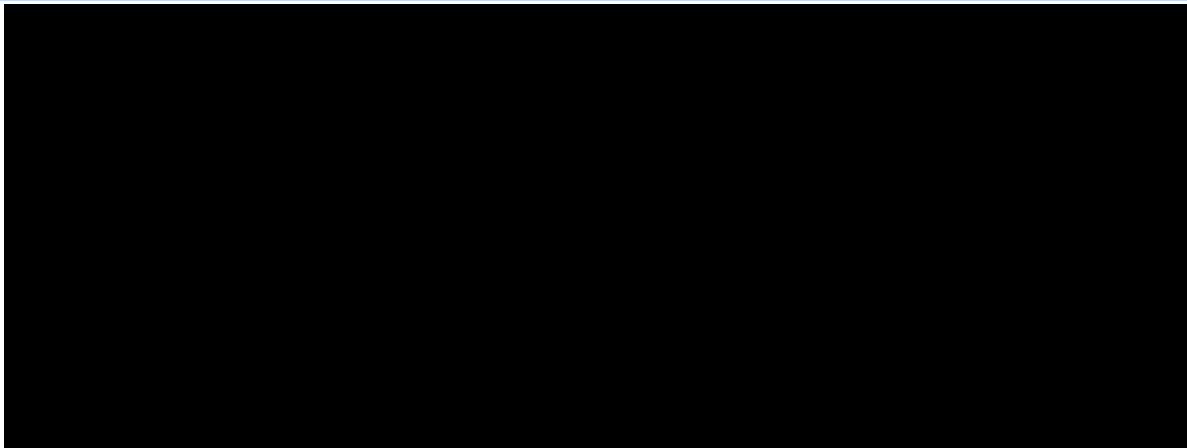
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DSS}$	600	V
Drain Current	$I_D(T_C=25^\circ C)$	12	A
	$I_D(T_C=100^\circ C)$	7.4	A
Drain Current - Pulsed	$I_{DM}$	48	A
Gate-Source Voltage	$V_{GSS}$	±30	V
Single Pulsed Avalanche Energy	$E_{AS}$	870	mJ
Repetitive Avalanche Energy	$E_{AR}$	22.5	mJ
Avalanche Current	$I_{AR}$	12	A
Power Dissipation	$P_D(T_C=25^\circ C)$	225	W
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	

**电性能参数 / Electrical Characteristics(Ta=25°C)**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V$ $I_D=250\mu A$	600			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=600V$ $V_{GS}=0V$			1	$\mu A$
		$V_{DS}=480V$ $T_C=125^\circ C$			10	$\mu A$
Gate-Body Leakage Current, Forward	$I_{GSS}$	$V_{GS}=\pm 30V$ $V_{DS}=0V$			±0.1	$\mu A$
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	2		4	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=6.0A$		0.53	0.65	
Forward Transconductance	$g_{FS}$	$V_{DS}=40V$ $I_D=6.0A$		13		S
Drain-Source Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V$ $I_S=12A$			1.4	V
Input Capacitance	$C_{iss}$	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0MHz$		1760	2290	pF
Output Capacitance	$C_{oss}$			182	235	pF
Reverse Transfer Capacitance	$C_{rss}$			21	28	pF
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=300V$ $I_D=12A$ $R_G=25$		30	70	ns
Turn-On Rise Time	$t_r$			85	180	ns
Turn-Off Delay Time	$t_{d(off)}$			140	280	ns
Turn-Off Fall Time	$t_f$			90	190	ns

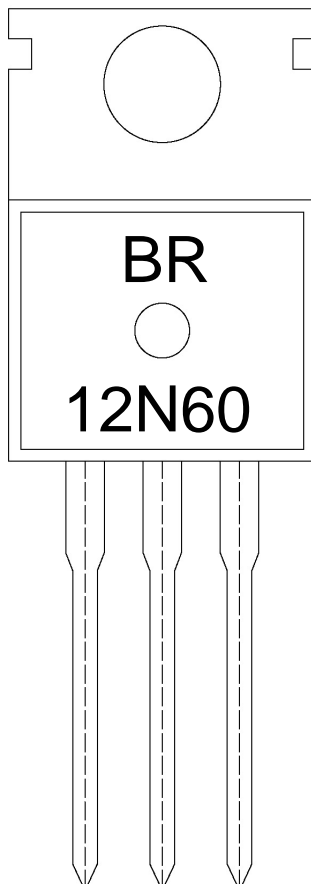


外形尺寸图 / Package Dimensions



Symbol	Dimensions in Millimeters		Symbol	Dimensions in Millimeters	
	Min	Max		Min	Max
$\Delta$	9.8	10.2	C	1.2	1.4
$\phi$	2.56	3.04	$\phi$	1.63	1.67
4	15.7	16.1	8	13.0	13.4
6	12.6	13.0	$a_1$	2.2	2.6
9	$b_1$	9.6	$a_1$	0.7	0.8
5	14.7	15.1	$a_1$	13.2	13.6
$E$	14.7	15.1	$E$	23.4	23.8
$a_2$	1.25	1.45			

印章说明 / Marking Instructions



BR

12N 60

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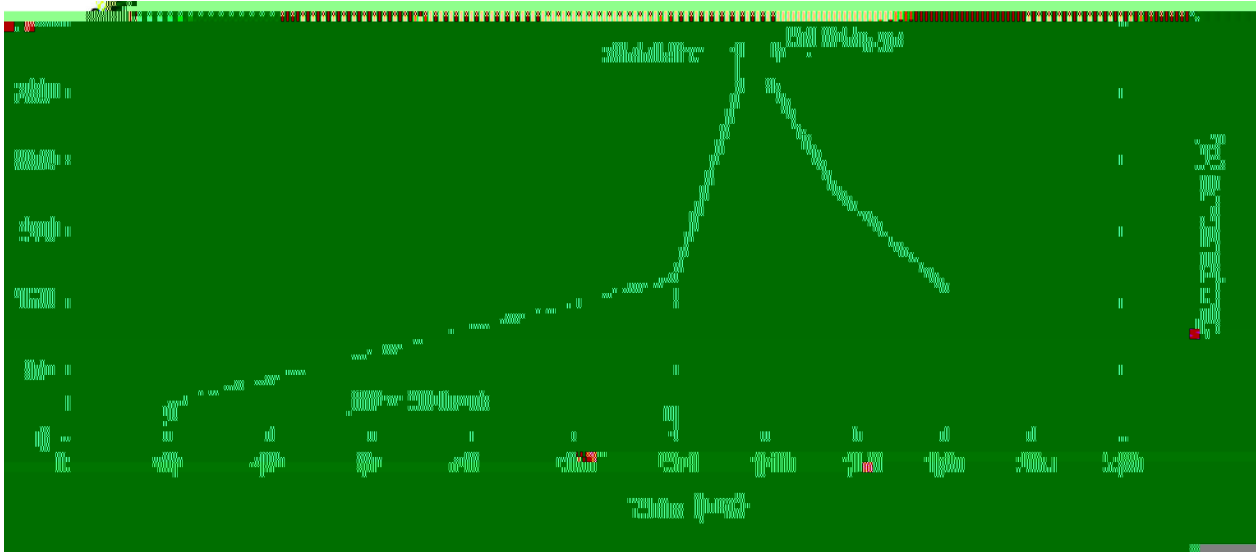
Note:

BR: Company Code

12N60: Product Type.

\*\*\*\*: Lot No. Code, code change with Lot No.

**波峰焊温度曲线图(无铅) / Temperature Profile for Dip Soldering(Pb-Free)**



Note:

- |   |        |           |   |
|---|--------|-----------|---|
| 1 | 25 150 | 60 90sec; | 1.Preheating:25~150 , Time:60~90sec.    |
| 2 | 255±5  | 5±0.5sec; | 2.Peak Temp.:255±5 , Duration:5±0.5sec. |
| 3 | 2 10   | /sec.     | 3. Cooling Speed: 2~10 /sec.            |

**耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions**

270±5                      10±1 sec.                      Temp.:270±5                      Time:10±1 sec

**包装规格 / Packaging SPEC.**

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm <sup>3</sup> )		
	只袋	袋盒	只盒	盒箱	只箱	袋	盒	箱

/ TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm <sup>3</sup> )		
	只套管	套管盒	只盒	盒箱	只箱	套管	盒	箱

**使用说明 / Notices**